

## ADG1408-EP/ADG1409-EP

### FEATURES

**4.7  $\Omega$  maximum on resistance @ 25°C**  
**0.5  $\Omega$  on resistance flatness**  
**Up to 190 mA continuous current**  
**Fully specified at  $\pm 15$  V/ $+12$  V/ $\pm 5$  V**  
**3 V logic-compatible inputs**  
**Rail-to-rail operation**  
**Break-before-make switching action**  
**16-lead TSSOP**

### ENHANCED PRODUCT FEATURES

**Supports defense and aerospace applications**  
**(AQEC standard)**  
**Military temperature range:  $-55^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$**   
**Controlled manufacturing baseline**  
**One assembly and test site**  
**One fabrication site**  
**Enhanced product change notification**  
**Qualification data available on request**

### GENERAL DESCRIPTION

The ADG1408-EP/ADG1409-EP are monolithic *i*CMOS® analog multiplexers comprising eight single channels and four differential channels, respectively. The ADG1408-EP switches one of eight inputs to a common output, as determined by the 3-bit binary address lines, A0, A1, and A2. The ADG1409-EP switches one of four differential inputs to a common differential output, as determined by the 2-bit binary address lines, A0 and A1. An EN input on both devices is used to enable or disable the device. When disabled, all channels are switched off.

The *i*CMOS (industrial CMOS) modular manufacturing process combines high voltage CMOS (complementary metal-oxide semiconductor) and bipolar technologies. It enables the development of a wide range of high performance analog ICs capable of 33 V operation in a footprint that no other generation of high voltage parts has been able to achieve. Unlike analog ICs using conventional CMOS processes, *i*CMOS components can tolerate high supply voltages while providing increased performance, dramatically lower power consumption, and reduced package size.

### FUNCTIONAL BLOCK DIAGRAM

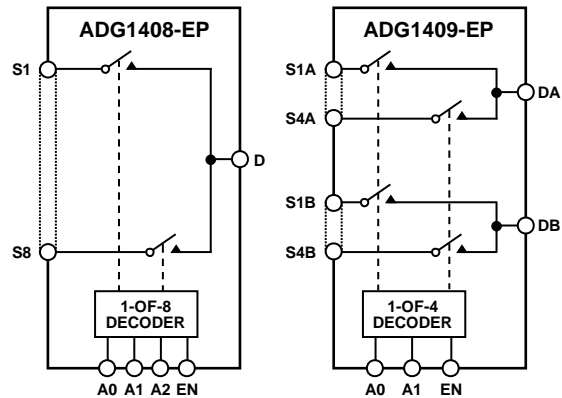


Figure 1.

The ultralow on resistance and on resistance flatness of these switches make them ideal solutions for data acquisition and gain switching applications where low distortion is critical. *i*CMOS construction ensures ultralow power dissipation, making the parts ideally suited for portable and battery-powered instruments.

Full details about this enhanced product are available in the ADG1408/ADG1409 data sheet, which should be consulted in conjunction with this data sheet.

### PRODUCT HIGHLIGHTS

1. 4  $\Omega$  on resistance
2. 0.5  $\Omega$  on resistance flatness
3. 3 V logic-compatible digital input,  $V_{INH} = 2.0$  V,  $V_{INL} = 0.8$  V
4. 16-lead TSSOP package

#### Rev. 0

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## REVISION HISTORY

3/11—Revision 0: Initial Version

# SPECIFICATIONS

## 15 V DUAL SUPPLY

$V_{DD} = +15\text{ V} \pm 10\%$ ,  $V_{SS} = -15\text{ V} \pm 10\%$ ,  $GND = 0\text{ V}$ , unless otherwise noted.

Table 1.

Parameter	+25°C	-55°C to +125°C	Unit	Test Conditions/Comments
<b>ANALOG SWITCH</b>				
Analog Signal Range		$V_{SS}$ to $V_{DD}$	V	
On Resistance ( $R_{ON}$ )	4		$\Omega$ typ	$V_S = \pm 10\text{ V}$ , $I_S = -10\text{ mA}$ ; see Figure 12
	4.7	6.7	$\Omega$ max	$V_{DD} = +13.5\text{ V}$ , $V_{SS} = -13.5\text{ V}$
On Resistance Match Between Channels ( $\Delta R_{ON}$ )	0.2		$\Omega$ typ	$V_S = \pm 10\text{ V}$ , $I_S = -10\text{ mA}$
	0.78	1.1	$\Omega$ max	
On Resistance Flatness ( $R_{FLAT(ON)}$ )	0.5		$\Omega$ typ	$V_S = \pm 10\text{ V}$ , $I_S = -10\text{ mA}$
	0.72	0.92	$\Omega$ max	
<b>LEAKAGE CURRENTS</b>				
Source Off Leakage, $I_S$ (Off)	$\pm 0.04$		nA typ	$V_{DD} = +16.5\text{ V}$ , $V_{SS} = -16.5\text{ V}$
	$\pm 0.2$	$\pm 5$	nA max	$V_S = \pm 10\text{ V}$ , $V_D = \mp 10\text{ V}$ ; see Figure 13
Drain Off Leakage, $I_D$ (Off)	$\pm 0.04$		nA typ	$V_S = \pm 10\text{ V}$ , $V_D = \mp 10\text{ V}$ ; see Figure 13
	$\pm 0.45$	$\pm 30$	nA max	
Channel On Leakage, $I_D$ , $I_S$ (On)	$\pm 0.1$		nA typ	$V_S = V_D = \pm 10\text{ V}$ ; see Figure 14
	$\pm 1.5$	$\pm 30$	nA max	
<b>DIGITAL INPUTS</b>				
Input High Voltage, $V_{INH}$		2.0	V min	
Input Low Voltage, $V_{INL}$		0.8	V max	
Input Current	$\pm 0.005$		$\mu\text{A}$ typ	$V_{IN} = V_{GND}$ or $V_{DD}$
		$\pm 0.1$	$\mu\text{A}$ max	
Digital Input Capacitance, $C_{IN}$	4		pF typ	
<b>DYNAMIC CHARACTERISTICS<sup>1</sup></b>				
Transition Time, $t_{TRANSITION}$	140		ns typ	$R_L = 100\ \Omega$ , $C_L = 35\text{ pF}$
	170	240	ns max	$V_S = 10\text{ V}$ , see Figure 15
Break-Before-Make Time Delay, $t_{BBM}$	50		ns typ	$R_L = 100\ \Omega$ , $C_L = 35\text{ pF}$
		19	ns min	$V_{S1} = V_{S2} = 10\text{ V}$ ; see Figure 16
$t_{ON}$ (EN)	100		ns typ	$R_L = 100\ \Omega$ , $C_L = 35\text{ pF}$
	120	165	ns max	$V_S = 10\text{ V}$ ; see Figure 17
$t_{OFF}$ (EN)	100		ns typ	$R_L = 100\ \Omega$ , $C_L = 35\text{ pF}$
	120	170	ns max	$V_S = 10\text{ V}$ ; see Figure 17
Charge Injection	-50		pC typ	$V_S = 0\text{ V}$ , $R_S = 0\ \Omega$ , $C_L = 1\text{ nF}$ ; see Figure 18
Off Isolation	-70		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; see Figure 19
Channel-to-Channel Crosstalk	-70		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; see Figure 20
Total Harmonic Distortion, THD + N	0.025		% typ	$R_L = 110\ \Omega$ , $15\text{ V p-p}$ , $f = 20\text{ Hz to } 20\text{ kHz}$ ; see Figure 22
-3 dB Bandwidth				$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ ; see Figure 21
ADG1408-EP	60		MHz typ	
ADG1409-EP	115		MHz typ	
Insertion Loss	0.24		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; see Figure 21
$C_S$ (Off)	14		pF typ	$f = 1\text{ MHz}$
$C_D$ (Off)				
ADG1408-EP	80		pF typ	$f = 1\text{ MHz}$
ADG1409-EP	40		pF typ	$f = 1\text{ MHz}$
$C_D$ , $C_S$ (On)				
ADG1408-EP	135		pF typ	$f = 1\text{ MHz}$
ADG1409-EP	90		pF typ	$f = 1\text{ MHz}$

# ADG1408-EP/ADG1409-EP

Parameter	+25°C	-55°C to +125°C	Unit	Test Conditions/Comments
<b>POWER REQUIREMENTS</b>				
$I_{DD}$	0.002	1	$\mu\text{A typ}$	$V_{DD} = +16.5\text{ V}, V_{SS} = -16.5\text{ V}$ Digital inputs = 0 V or $V_{DD}$
	220		$\mu\text{A max}$	Digital inputs = 5 V
$I_{SS}$	0.002	420	$\mu\text{A typ}$	Digital inputs = 0 V, 5 V or $V_{DD}$
		1	$\mu\text{A max}$	
$V_{DD}/V_{SS}$		$\pm 4.5/\pm 16.5$	V min/max	

<sup>1</sup> Guaranteed by design, not subject to production test.

**12 V SINGLE SUPPLY**

$V_{DD} = 12\text{ V} \pm 10\%$ ,  $V_{SS} = 0\text{ V}$ ,  $GND = 0\text{ V}$ , unless otherwise noted.

**Table 2.**

Parameter	+25°C	-55°C to +125°C	Unit	Test Conditions/Comments
<b>ANALOG SWITCH</b>				
Analog Signal Range		0 to $V_{DD}$	V	
On Resistance ( $R_{ON}$ )	6		$\Omega$ typ	$V_S = 0\text{ V to }10\text{ V}$ , $I_S = -10\text{ mA}$ ; see Figure 12
	8	11.2	$\Omega$ max	$V_{DD} = 10.8\text{ V}$ , $V_{SS} = 0\text{ V}$
On Resistance Match	0.2		$\Omega$ typ	$V_S = 0\text{ V to }10\text{ V}$ , $I_S = -10\text{ mA}$
Between Channels ( $\Delta R_{ON}$ )	0.82	1.1	$\Omega$ max	
On Resistance Flatness ( $R_{FLAT(ON)}$ )	1.5		$\Omega$ typ	$V_S = 0\text{ V to }10\text{ V}$ , $I_S = -10\text{ mA}$
	2.5	2.8	$\Omega$ max	
<b>LEAKAGE CURRENTS</b>				
Source Off Leakage, $I_S$ (Off)	$\pm 0.04$		nA typ	$V_{DD} = 13.2\text{ V}$ $V_S = 1\text{ V}/10\text{ V}$ , $V_D = 10\text{ V}/1\text{ V}$ ; see Figure 13
	$\pm 0.2$	$\pm 5$	nA max	
Drain Off Leakage, $I_D$ (Off)	$\pm 0.04$		nA typ	$V_S = 1\text{ V}/10\text{ V}$ , $V_D = 10\text{ V}/1\text{ V}$ ; see Figure 13
	$\pm 0.45$	$\pm 37$	nA max	
Channel On Leakage, $I_D$ , $I_S$ (On)	$\pm 0.06$		nA typ	$V_S = V_D = 1\text{ V or }10\text{ V}$ ; see Figure 14
	$\pm 0.44$	$\pm 32$	nA max	
<b>DIGITAL INPUTS</b>				
Input High Voltage, $V_{INH}$		2.0	V min	
Input Low Voltage, $V_{INL}$		0.8	V max	
Input Current	$\pm 0.005$		$\mu\text{A}$ typ	$V_{IN} = V_{GND}$ or $V_{DD}$
		$\pm 0.1$	$\mu\text{A}$ max	
Digital Input Capacitance, $C_{IN}$	5		pF typ	
<b>DYNAMIC CHARACTERISTICS<sup>1</sup></b>				
Transition Time, $t_{TRANSITION}$	200		ns typ	$R_L = 100\ \Omega$ , $C_L = 35\text{ pF}$
	260	380	ns max	$V_S = 8\text{ V}$ ; see Figure 15
Break-Before-Make Time Delay, $t_{BBM}$	90		ns typ	$R_L = 100\ \Omega$ , $C_L = 35\text{ pF}$
		40	ns min	$V_{S1} = V_{S2} = 8\text{ V}$ ; see Figure 16
$t_{ON}$ (EN)	160		ns typ	$R_L = 100\ \Omega$ , $C_L = 35\text{ pF}$
	210	285	ns max	$V_S = 8\text{ V}$ ; see Figure 17
$t_{OFF}$ (EN)	115		ns typ	$R_L = 100\ \Omega$ , $C_L = 35\text{ pF}$
	145	200	ns max	$V_S = 8\text{ V}$ ; see Figure 17
Charge Injection	-12		pC typ	$V_S = 6\text{ V}$ , $R_S = 0\ \Omega$ , $C_L = 1\text{ nF}$ ; see Figure 18
Off Isolation	-70		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; see Figure 19
Channel-to-Channel Crosstalk	-70		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; see Figure 20
-3 dB Bandwidth				$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ ; see Figure 21
ADG1408-EP	36		MHz typ	
ADG1409-EP	72		MHz typ	
Insertion Loss	0.5		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; see Figure 21
$C_S$ (Off)	25		pF typ	$f = 1\text{ MHz}$
$C_D$ (Off)				
ADG1408-EP	165		pF typ	$f = 1\text{ MHz}$
ADG1409-EP	80		pF typ	$f = 1\text{ MHz}$
$C_D$ , $C_S$ (On)				
ADG1408-EP	200		pF typ	$f = 1\text{ MHz}$
ADG1409-EP	120		pF typ	$f = 1\text{ MHz}$

# ADG1408-EP/ADG1409-EP

Parameter	+25°C	-55°C to +125°C	Unit	Test Conditions/Comments
POWER REQUIREMENTS				$V_{DD} = 13.2\text{ V}$
$I_{DD}$	0.002	1	$\mu\text{A typ}$ $\mu\text{A max}$	Digital inputs = 0 V or $V_{DD}$
	220	420	$\mu\text{A typ}$ $\mu\text{A max}$	Digital inputs = 5 V
$V_{DD}$		5/16.5	V min/max	$V_{SS} = 0\text{ V}$ , GND = 0 V

<sup>1</sup> Guaranteed by design, not subject to production test.

**5 V DUAL SUPPLY**

$V_{DD} = +5\text{ V} \pm 10\%$ ,  $V_{SS} = -5\text{ V} \pm 10\%$ ,  $GND = 0\text{ V}$ , unless otherwise noted.

**Table 3.**

Parameter	+25°C	-55°C to +125°C	Unit	Test Conditions/Comments
<b>ANALOG SWITCH</b>				
Analog Signal Range		$V_{SS}$ to $V_{DD}$	V	
On Resistance ( $R_{ON}$ )	7		$\Omega$ typ	$V_S = \pm 4.5\text{ V}$ , $I_S = -10\text{ mA}$ ; see Figure 12
	9	12	$\Omega$ max	$V_{DD} = +4.5\text{ V}$ , $V_{SS} = -4.5\text{ V}$
On Resistance Match Between Channels ( $\Delta R_{ON}$ )	0.3		$\Omega$ typ	$V_S = \pm 4.5\text{ V}$ , $I_S = -10\text{ mA}$
	0.78	1.1	$\Omega$ max	
On Resistance Flatness ( $R_{FLAT(ON)}$ )	1.5		$\Omega$ typ	$V_S = \pm 4.5\text{ V}$ ; $I_S = -10\text{ mA}$
	2.5	3	$\Omega$ max	
<b>LEAKAGE CURRENTS</b>				
Source Off Leakage, $I_S$ (Off)	$\pm 0.02$		nA typ	$V_{DD} = +5.5\text{ V}$ , $V_{SS} = -5.5\text{ V}$
	$\pm 0.2$	$\pm 5$	nA max	$V_S = \pm 4.5\text{ V}$ , $V_D = \mp 4.5\text{ V}$ ; see Figure 13
Drain Off Leakage, $I_D$ (Off)	$\pm 0.02$		nA typ	$V_S = \pm 4.5\text{ V}$ , $V_D = \mp 4.5\text{ V}$ ; see Figure 13
	$\pm 0.45$	$\pm 20$	nA max	
Channel On Leakage, $I_D$ , $I_S$ (On)	$\pm 0.04$		nA typ	$V_S = V_D = \pm 4.5\text{ V}$ ; see Figure 14
	$\pm 0.3$	$\pm 22$	nA max	
<b>DIGITAL INPUTS</b>				
Input High Voltage, $V_{INH}$		2.0	V min	
Input Low Voltage, $V_{INL}$		0.8	V max	
Input Current	$\pm 0.005$		$\mu\text{A}$ typ	$V_{IN} = V_{GND}$ or $V_{DD}$
		$\pm 0.1$	$\mu\text{A}$ max	
Digital Input Capacitance, $C_{IN}$	5		pF typ	
<b>DYNAMIC CHARACTERISTICS<sup>1</sup></b>				
Transition Time, $t_{TRANSITION}$	330		ns typ	$R_L = 100\ \Omega$ , $C_L = 35\text{ pF}$
	440	550	ns max	$V_S = 5\text{ V}$ ; see Figure 15
Break-Before-Make Time Delay, $t_{BBM}$	100		ns typ	$R_L = 100\ \Omega$ , $C_L = 35\text{ pF}$
		45	ns min	$V_{S1} = V_{S2} = 5\text{ V}$ ; see Figure 16
$t_{ON}$ (EN)	245		ns typ	$R_L = 100\ \Omega$ , $C_L = 35\text{ pF}$
	330	440	ns max	$V_S = 5\text{ V}$ ; see Figure 17
$t_{OFF}$ (EN)	215		ns typ	$R_L = 100\ \Omega$ , $C_L = 35\text{ pF}$
	285	370	ns max	$V_S = 5\text{ V}$ ; see Figure 17
Charge Injection	-10		pC typ	$V_S = 0\text{ V}$ , $R_S = 0\ \Omega$ , $C_L = 1\text{ nF}$ ; see Figure 18
Off Isolation	-70		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; see Figure 19
Channel-to-Channel Crosstalk	-70		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; see Figure 20
Total Harmonic Distortion, THD + N	0.06		% typ	$R_L = 110\ \Omega$ , $5\text{ V p-p}$ , $f = 20\text{ Hz to } 20\text{ kHz}$ ; see Figure 22
-3 dB Bandwidth				$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ ; see Figure 21
ADG1408-EP	40		MHz typ	
ADG1409-EP	80		MHz typ	
Insertion Loss	0.5		dB typ	$R_L = 50\ \Omega$ , $C_L = 5\text{ pF}$ , $f = 1\text{ MHz}$ ; see Figure 21
$C_S$ (Off)	20		pF typ	$f = 1\text{ MHz}$
$C_D$ (Off)				
ADG1408-EP	130		pF typ	$f = 1\text{ MHz}$
ADG1409-EP	65		pF typ	$f = 1\text{ MHz}$
$C_D$ , $C_S$ (On)				
ADG1408-EP	180		pF typ	$f = 1\text{ MHz}$
ADG1409-EP	120		pF typ	$f = 1\text{ MHz}$

# ADG1408-EP/ADG1409-EP

Parameter	+25°C	-55°C to +125°C	Unit	Test Conditions/Comments
<b>POWER REQUIREMENTS</b>				
$I_{DD}$	0.001	1	$\mu\text{A typ}$ $\mu\text{A max}$	$V_{DD} = +5.5\text{ V}, V_{SS} = -5.5\text{ V}$ Digital inputs = 0 V or $V_{DD}$
$I_{SS}$	0.001	1	$\mu\text{A typ}$ $\mu\text{A max}$	Digital inputs = 0 V, 5 V or $V_{DD}$
$V_{DD}/V_{SS}$		$\pm 4.5/\pm 16.5$	V min/max	

<sup>1</sup> Guaranteed by design, not subject to production test.

## CONTINUOUS CURRENT PER CHANNEL, S OR D

Table 4.

Parameter	25°C	85°C	125°C	Unit	Test Conditions/Comments
<b>CONTINUOUS CURRENT, S or D<sup>1</sup></b>					
15 V Dual Supply					
ADG1408-EP	190	105	50	mA max	$V_{DD} = +13.5\text{ V}, V_{SS} = -13.5\text{ V}$
ADG1409-EP	140	85	45	mA max	
12 V Single Supply					
ADG1408-EP	160	95	50	mA max	$V_{DD} = 10.8\text{ V}, V_{SS} = 0\text{ V}$
ADG1409-EP	120	75	40	mA max	
5 V Dual Supply					
ADG1408-EP	155	90	45	mA max	$V_{DD} = +4.5\text{ V}, V_{SS} = -4.5\text{ V}$
ADG1409-EP	115	70	40	mA max	

<sup>1</sup> Guaranteed by design, not subject to production test.



## ABSOLUTE MAXIMUM RATINGS

$T_A = 25^\circ\text{C}$ , unless otherwise noted.

Table 5.

Parameter	Rating
$V_{DD}$ to $V_{SS}$	35 V
$V_{DD}$ to GND	-0.3 V to +25 V
$V_{SS}$ to GND	+0.3 V to -25 V
Analog Inputs, Digital Inputs <sup>1</sup>	$V_{SS} - 0.3\text{ V}$ to $V_{DD} + 0.3\text{ V}$ or 30 mA, whichever occurs first
Continuous Current, S or D	Table 4 data + 10%
Peak Current, S or D (Pulsed at 1 ms, 10% Duty Cycle Maximum)	350 mA
Operating Temperature Range	-55°C to +125°C
Storage Temperature Range	-65°C to +150°C
Junction Temperature	150°C
$\theta_{JA}$	150.4°C/W
$\theta_{JC}$	50°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	215°C
Infrared (15 sec)	220°C

<sup>1</sup> Overvoltages at A, EN, S, or D are clamped by internal diodes. Current should be limited to the maximum ratings given.

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Only one absolute maximum rating can be applied at any one time.

### ESD CAUTION



#### ESD (electrostatic discharge) sensitive device.

Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

# ADG1408-EP/ADG1409-EP

## PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

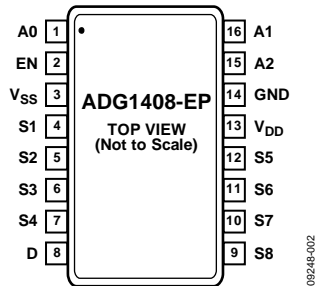


Figure 2. ADG1408-EP Pin Configuration

Table 6. ADG1408-EP Pin Function Descriptions

Pin No.		Mnemonic	Description
TSSOP	LFCSOP		
1	15	A0	Logic Control Input.
2	16	EN	Active High Digital Input. When low, the device is disabled and all switches are off. When high, Ax logic inputs determine on switches.
3	1	V <sub>SS</sub>	Most Negative Power Supply Potential. In single supply applications, it can be connected to ground.
4	2	S1	Source Terminal 1. Can be an input or an output.
5	3	S2	Source Terminal 2. Can be an input or an output.
6	4	S3	Source Terminal 3. Can be an input or an output.
7	5	S4	Source Terminal 4. Can be an input or an output.
8	6	D	Drain Terminal. Can be an input or an output.
9	7	S8	Source Terminal 8. Can be an input or an output.
10	8	S7	Source Terminal 7. Can be an input or an output.
11	9	S6	Source Terminal 6. Can be an input or an output.
12	10	S5	Source Terminal 5. Can be an input or an output.
13	11	V <sub>DD</sub>	Most Positive Power Supply Potential.
14	12	GND	Ground (0 V) Reference.
15	13	A2	Logic Control Input.
16	14	A1	Logic Control Input.
	EP	Exposed pad	The exposed pad is connected internally. For increased reliability of the solder joints and maximum thermal capability, it is recommended that the pad be soldered to the substrate, V <sub>SS</sub> .

Table 7. ADG1408-EP Truth Table

A2	A1	A0	EN	On Switch
X	X	X	0	None
0	0	0	1	1
0	0	1	1	2
0	1	0	1	3
0	1	1	1	4
1	0	0	1	5
1	0	1	1	6
1	1	0	1	7
1	1	1	1	8

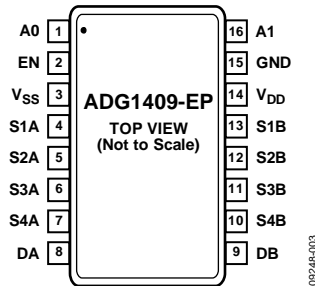


Figure 3. ADG1409-EP Pin Configuration (TSSOP)

Table 8. ADG1409-EP Pin Function Descriptions

Pin No.		Mnemonic	Description
TSSOP	LFCSP		
1	15	A0	Logic Control Input.
2	16	EN	Active High Digital Input. When low, the device is disabled and all switches are off. When high, Ax logic inputs determine on switches.
3	1	V <sub>SS</sub>	Most Negative Power Supply Potential. In single supply applications, it can be connected to ground.
4	2	S1A	Source Terminal 1A. Can be an input or an output.
5	3	S2A	Source Terminal 2A. Can be an input or an output.
6	4	S3A	Source Terminal 3A. Can be an input or an output.
7	5	S4A	Source Terminal 4A. Can be an input or an output.
8	6	DA	Drain Terminal A. Can be an input or an output.
9	7	DB	Drain Terminal B. Can be an input or an output.
10	8	S4B	Source Terminal 4B. Can be an input or an output.
11	9	S3B	Source Terminal 3B. Can be an input or an output.
12	10	S2B	Source Terminal 2B. Can be an input or an output.
13	11	S1B	Source Terminal 1B. Can be an input or an output.
14	12	V <sub>DD</sub>	Most Positive Power Supply Potential.
15	13	GND	Ground (0 V) Reference.
16	14	A1	Logic Control Input.
	EP	Exposed pad	The exposed pad is connected internally. For increased reliability of the solder joints and maximum thermal capability, it is recommended that the pad be soldered to the substrate, V <sub>SS</sub> .

Table 9. ADG1409-EP Truth Table

A1	A0	EN	On Switch Pair
X	X	0	None
0	0	1	1
0	1	1	2
1	0	1	3
1	1	1	4

## TYPICAL PERFORMANCE CHARACTERISTICS

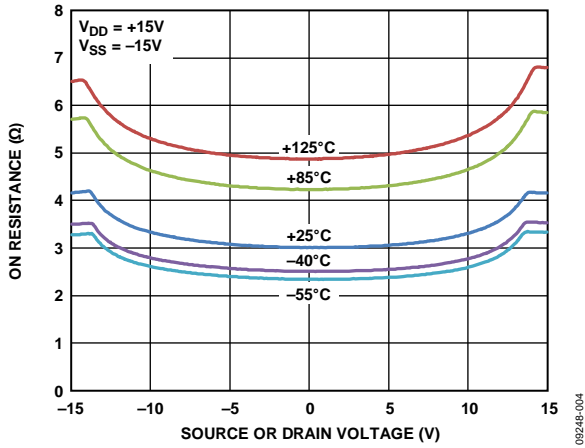


Figure 4. On Resistance vs.  $V_D$ ,  $V_S$  for Different Temperatures; 15 V Dual Supply

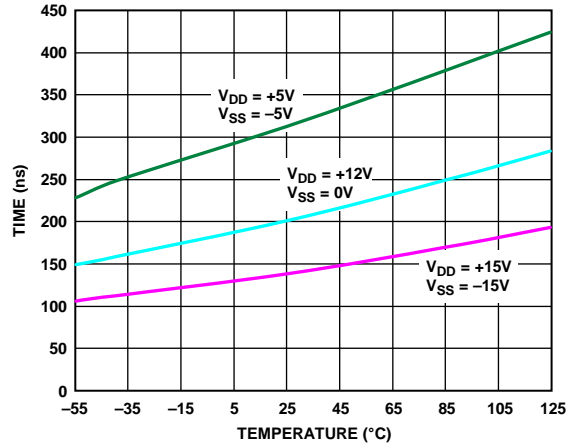


Figure 7. Transition Time vs. Temperature

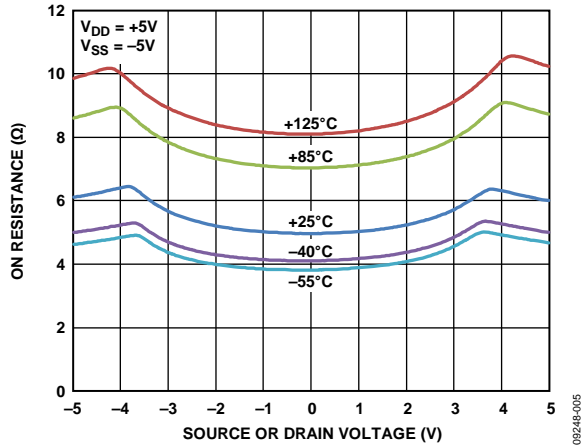


Figure 5. On Resistance vs.  $V_D$ ,  $V_S$  for Different Temperatures; 5 V Dual Supply

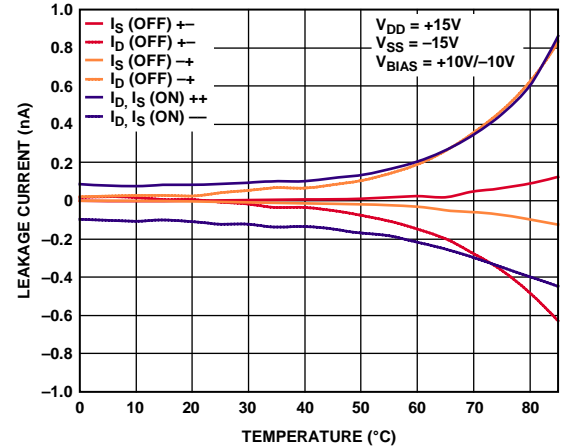


Figure 8. Leakage Current vs. Temperature; 15 V Dual Supply

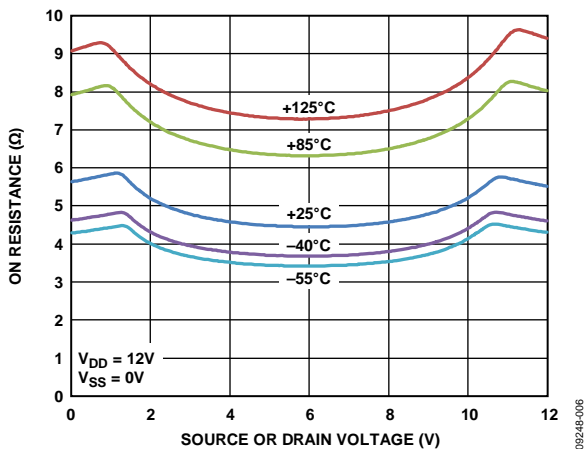


Figure 6. On Resistance vs.  $V_D$ ,  $V_S$  for Different Temperatures; 12 V Single Supply

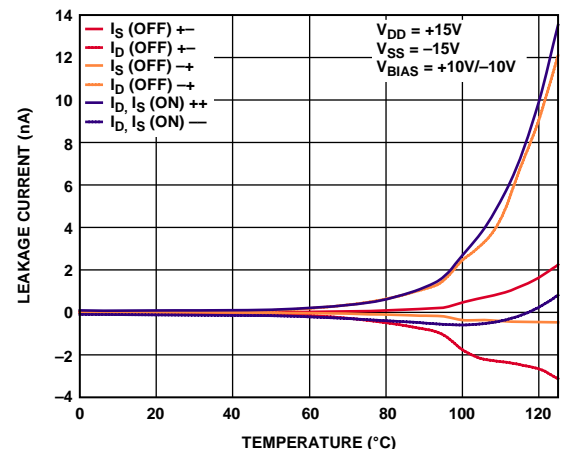


Figure 9. Leakage Current vs. Temperature; 15 V Dual Supply

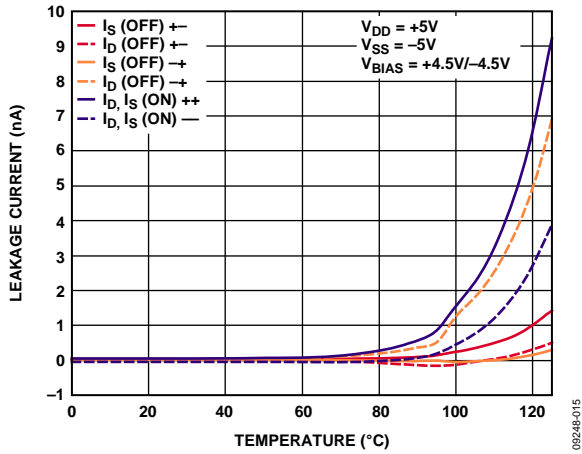


Figure 10. Leakage Current vs. Temperature;  
5 V Dual Supply

09248-015

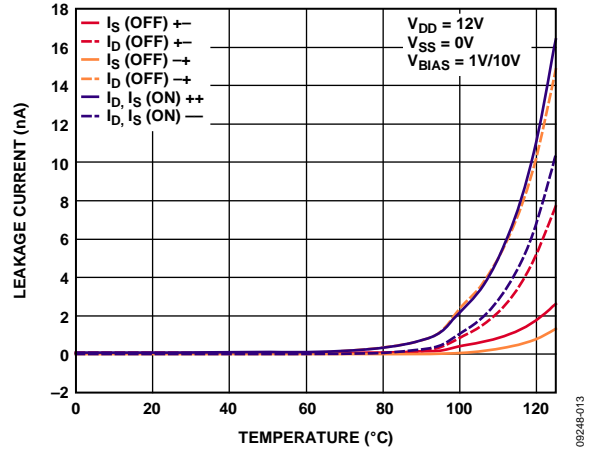


Figure 11. Leakage Current vs. Temperature;  
12 V Single Supply

09248-013

# ADG1408-EP/ADG1409-EP

## TEST CIRCUITS

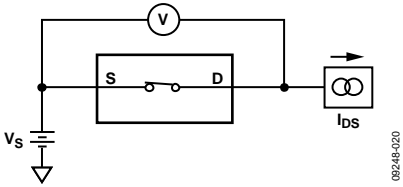


Figure 12. On Resistance

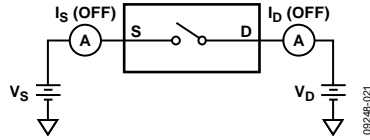


Figure 13. Off Leakage

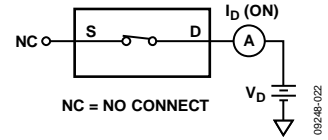


Figure 14. On Leakage

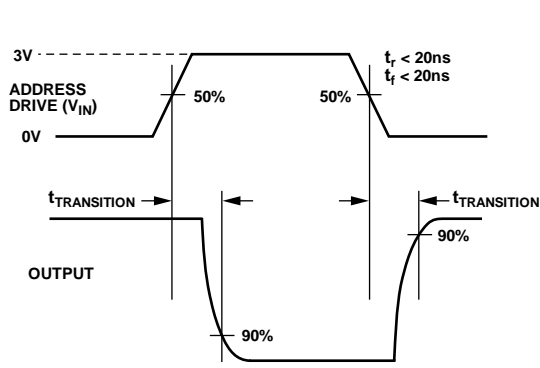
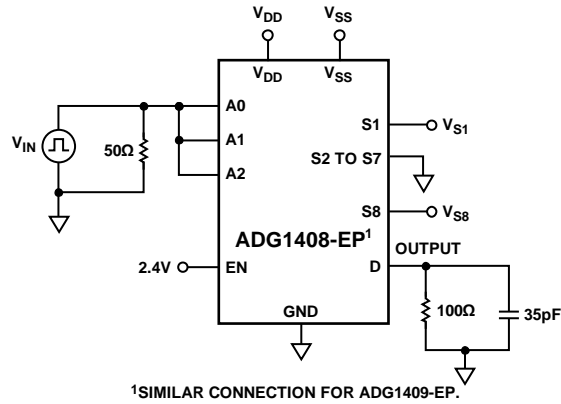


Figure 15. Address to Output Switching Times,  $t_{\text{TRANSITION}}$



09248-023

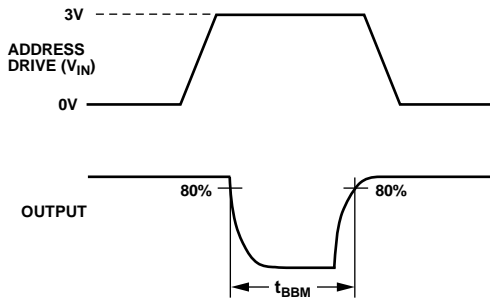
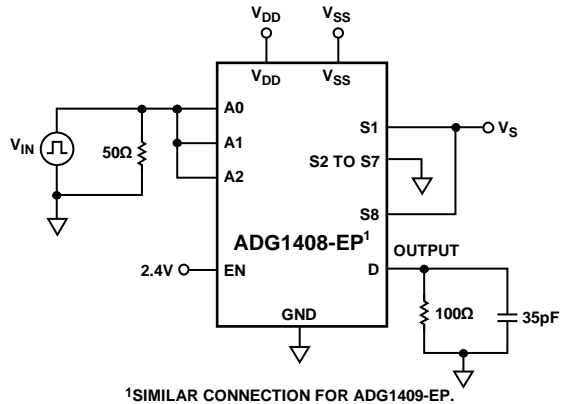


Figure 16. Break-Before-Make Delay,  $t_{\text{BBM}}$



09248-024

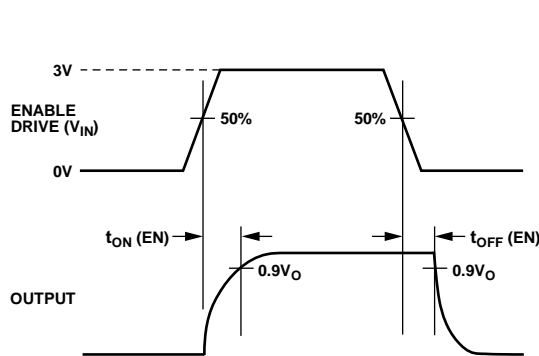
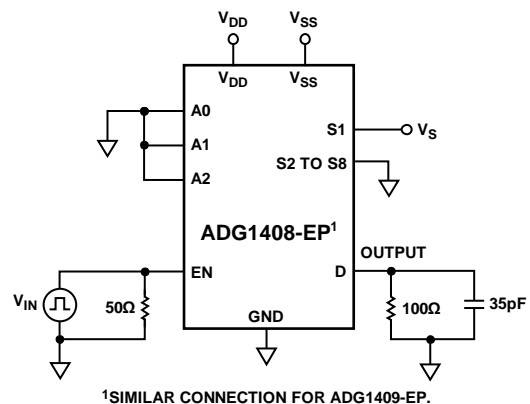


Figure 17. Enable Delay,  $t_{\text{ON}}(\text{EN})$ ,  $t_{\text{OFF}}(\text{EN})$



09248-025

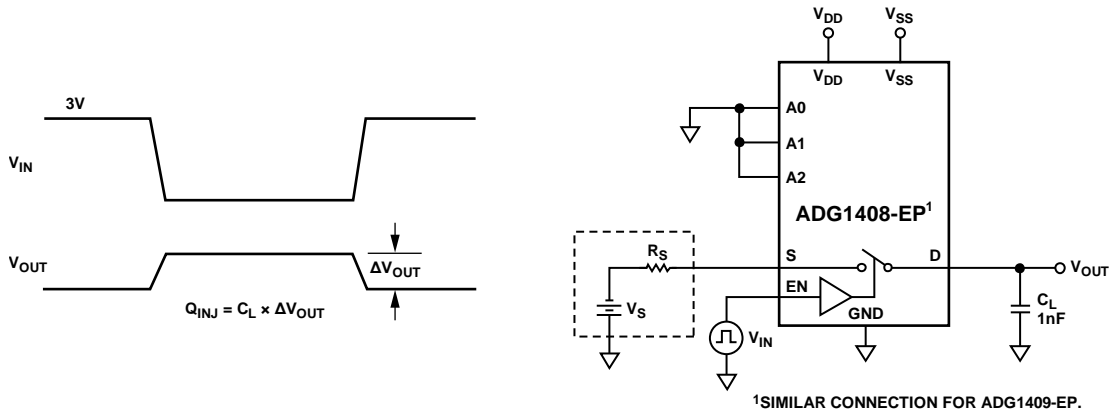


Figure 18. Charge Injection

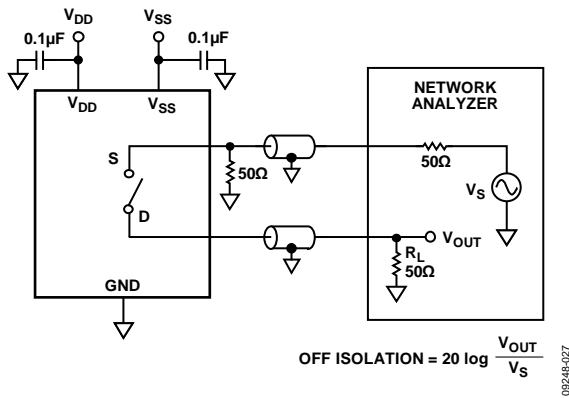


Figure 19. Off Isolation

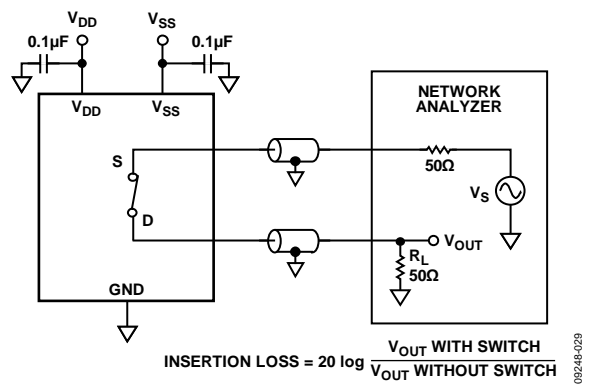


Figure 21. Insertion Loss

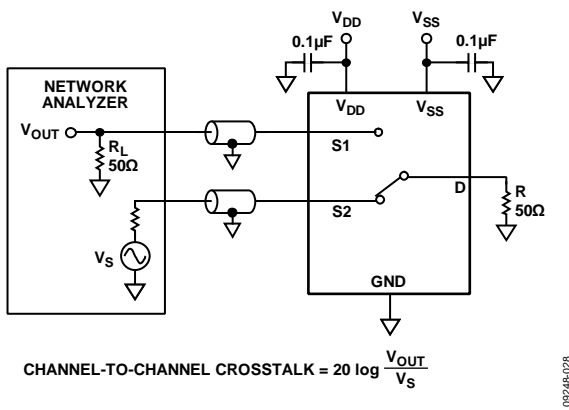


Figure 20. Channel-to-Channel Crosstalk

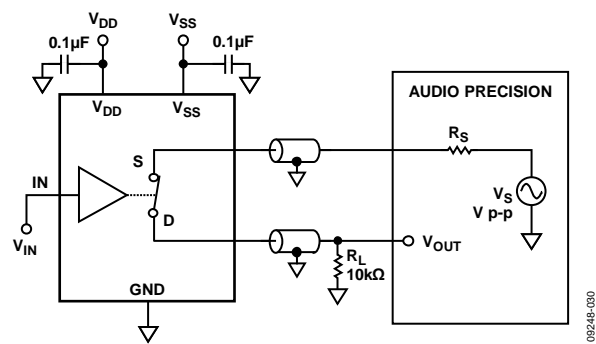


Figure 22. THD + Noise

# ADG1408-EP/ADG1409-EP

## OUTLINE DIMENSIONS

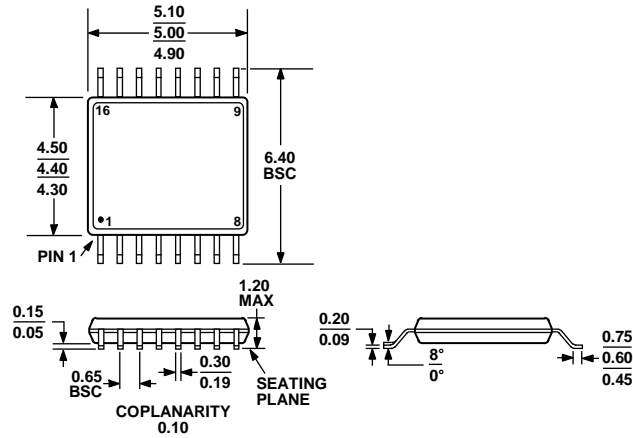


Figure 23. 16-Lead Thin Shrink Small Outline Package [TSSOP] (RU-16)

Dimensions shown in millimeters

## ORDERING GUIDE

Model	Temperature Range	Package Description	Package Option
ADG1408SRU-EP	-55°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG1408SRU-EP-RL7	-55°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG1409SRU-EP	-55°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16
ADG1409SRU-EP-RL7	-55°C to +125°C	16-Lead Thin Shrink Small Outline Package [TSSOP]	RU-16





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### Наши контакты:

**Телефон:** +7 812 627 14 35

**Электронная почта:** [sales@st-electron.ru](mailto:sales@st-electron.ru)

**Адрес:** 198099, Санкт-Петербург,  
Промышленная ул, дом № 19, литера Н,  
помещение 100-Н Офис 331